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UNITED STATES PATENT AND TRADEMARK OFFICE CERTIFICATE OF CORRECTION

PATENT NO. : 7,427,555

PAGE 1 of 1

DATED : September 23, 2008

INVENTOR(S) : Haskell et al.

It is certified that error appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

Page 4:

Please insert --GU, S. et al., "The Impact of initial growth and substrate nitridation on thick GaN growth on sapphire by hydride vapor phase epitaxy", Journal of Crystal Growth, North-Holland Publishing, Amsterdam, NL, vol. 231, no. 3, October 2001 (2001-10), pages 342-351--.

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